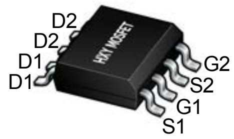
Description

The AO4630 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

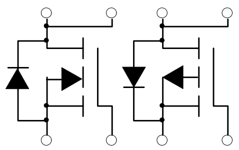
General Features

V_{DS} = 30V I_D =7A

$R_{DS(ON)}$ < 25mΩ @ V_{GS}=10V

V_{DS} = -30V I_D = -8.5A

$R_{DS(ON)}$ < 35mΩ @ V_{GS}= -10V



N-Channel and P-Channel

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AO4630	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Ch	P-Ch	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	±20	±20	V
I_D@T_A=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	7	-8.5	A
I_D@T_A=100˚C	Continuous Drain Current, V_{GS} @ 10V[1]	6	-4.6	A
I_{DM}	Pulsed Drain Current[2]	20	-28	A
EAS	Single Pulse Avalanche Energy[3]	72	62	mJ
I_{AS}	Avalanche Current	21	-19	A
P_D@T_A=25˚C	Total Power Dissipation[4]	2.5	3.08	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	˚C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	45		˚C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	30		˚C/W

N-Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.034	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=6A	---	18	25	mΩ
		V_{GS}=4.5V , I_D=5A	---	25	31	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	1.5	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.8	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=30V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=15V , I_D=5A	---	10	---	S
R_g	Gate Resistance	V_{DS}=24V , V_{GS}=0V , f=1MHz	---	2.5	---	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=4.5V , I_D=6A	---	7.2	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	2.2	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=12V , V_{GS}=10V , R_G=3.3Ω I_D=5A	---	3.9	---	ns
T_r	Rise Time		---	9.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	14.5	---	
T_f	Fall Time		---	6.0	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , f=1MHz	---	370	---	pF
C_{oss}	Output Capacitance		---	54	---	
C_{rss}	Reverse Transfer Capacitance		---	40	---	
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=25V , L=0.1mH , I_{AS}=10A	16	---	---	mJ
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	7	A
I_{SM}	Pulsed Source Current[2,6]		---	---	20	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=5A , T_J=25℃	---	---	1.2	V

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=10A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

P-Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -30V, V_{GS}=0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±20V	-	-	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}= -10V, I_D= -7A	-	26	35	mΩ
		V_{GS}= -4.5V, I_D= -4A	-	38	54	
C_{iss}	Input Capacitance	V_{DS}= -15V, V_{GS}=0V, f=1.0MHz	-	982	-	pF
C_{oss}	Output Capacitance		-	135	-	pF
C_{rss}	Reverse Transfer Capacitance		-	109	-	pF
Q_g	Total Gate Charge	V_{DS}= -15V, I_D= -4A, V_{GS}= -10V	-	10	-	nC
Q_{gs}	Gate-Source Charge		-	2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	2.7	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= -15V, I_D= -7A, V_{GS}= -10V, R_{GEN}=2.5Ω	-	11	-	ns
t_r	Turn-on Rise Time		-	19	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	45	-	ns
t_f	Turn-off Fall Time		-	26	-	ns
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-8.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-28	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -7A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

N-Typical Characteristics

Figure1: Output Characteristics

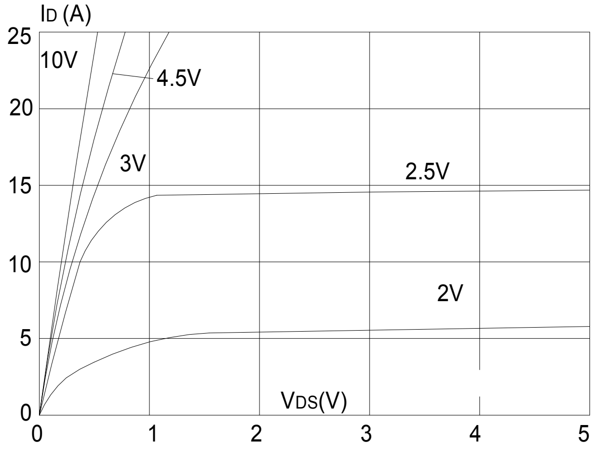


Figure 2: Typical Transfer Characteristics

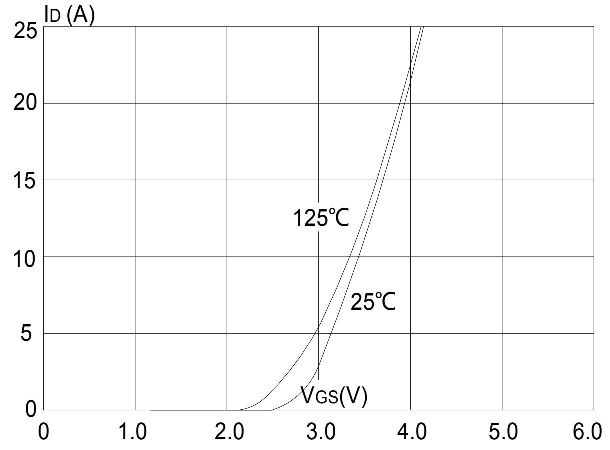


Figure 3: On-resistance vs. Drain Current

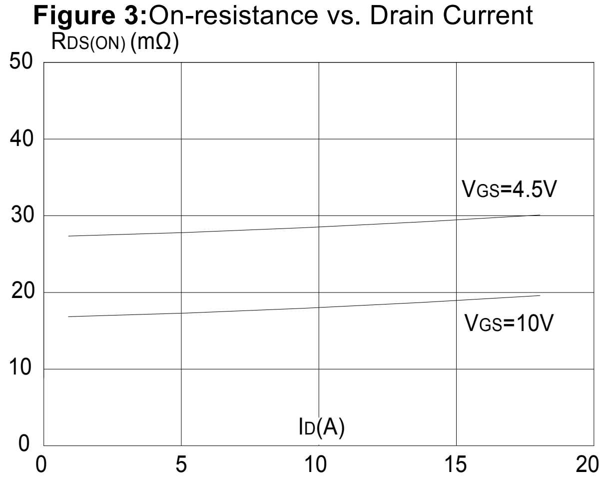


Figure 4: Body Diode Characteristics

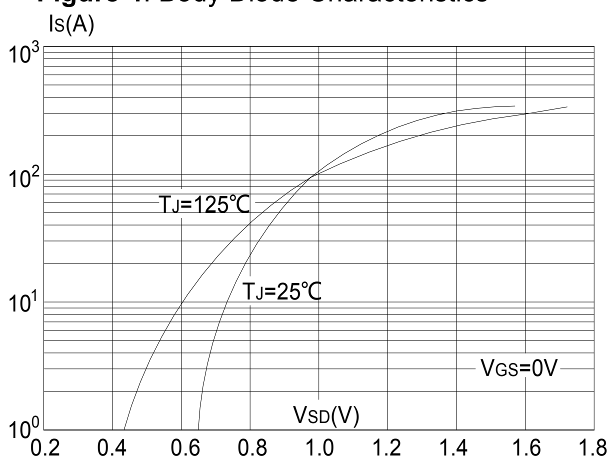


Figure 5: Gate Charge Characteristics

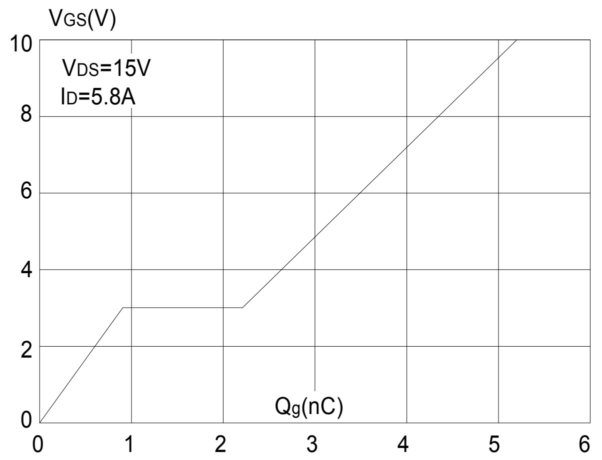


Figure 6: Capacitance Characteristics

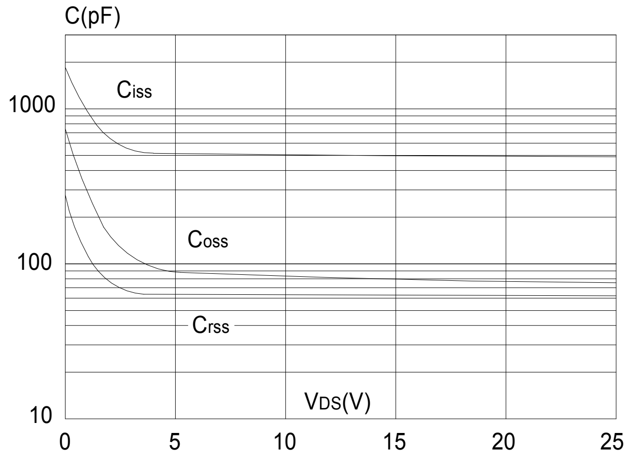


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

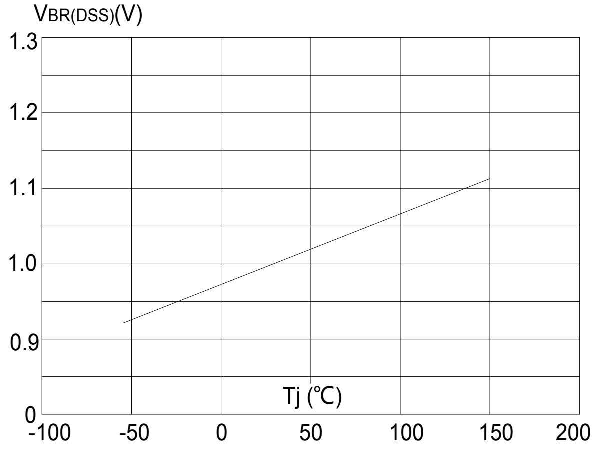


Figure 8: Normalized on Resistance vs. Junction Temperature

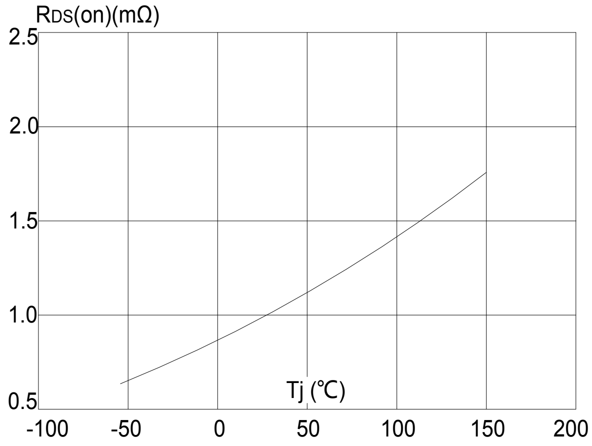


Figure 9: Maximum Safe Operating Area

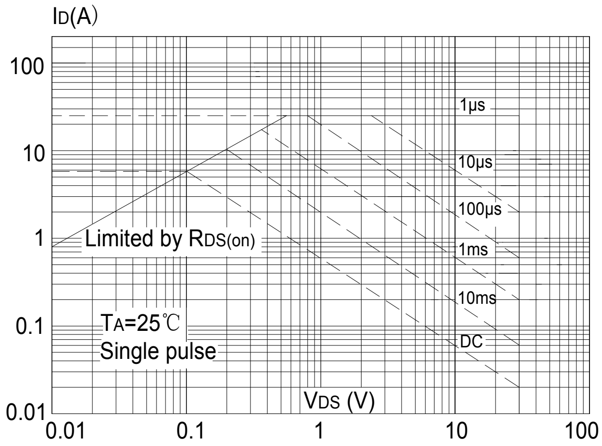


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

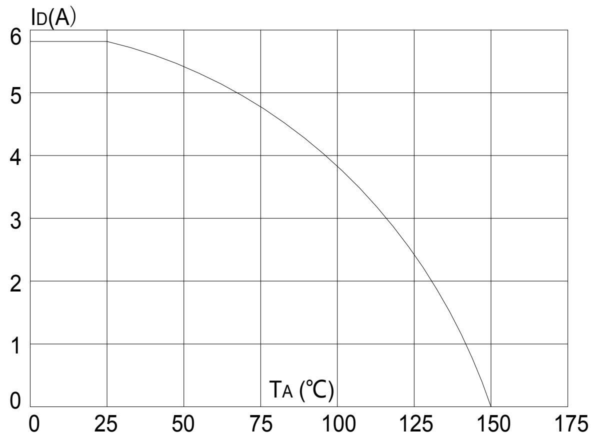
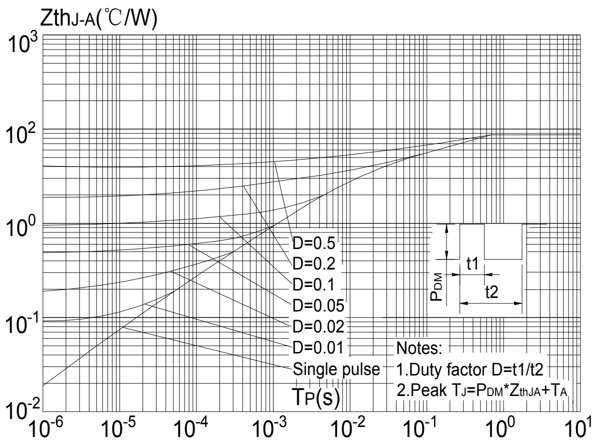


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



P-Typical Characteristics

Figure1: Output Characteristics

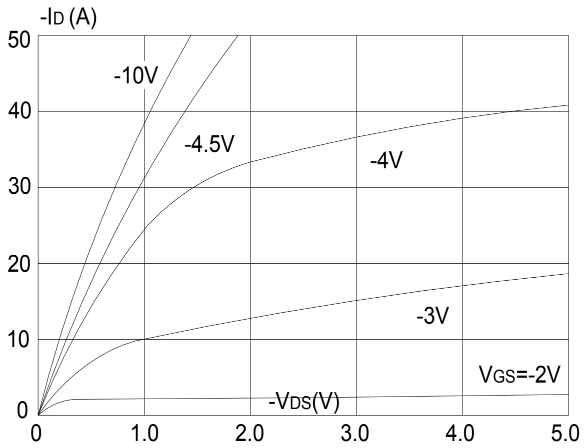


Figure 2: Typical Transfer Characteristics

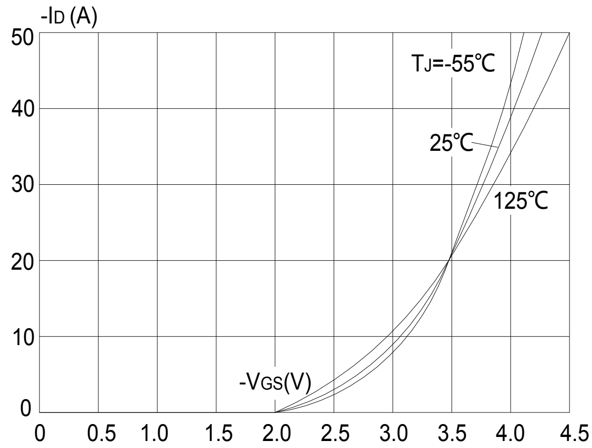


Figure 3: On-resistance vs. Drain Current

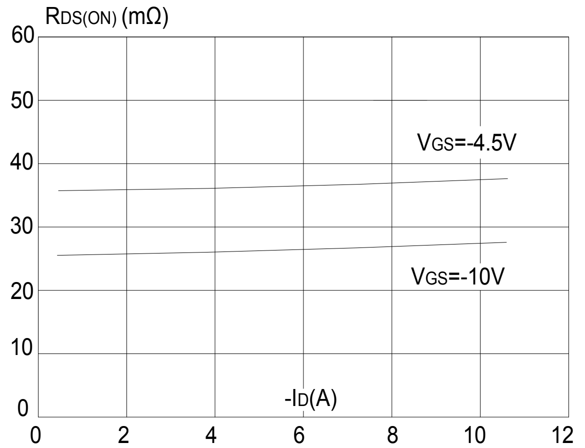


Figure 4: Body Diode Characteristics

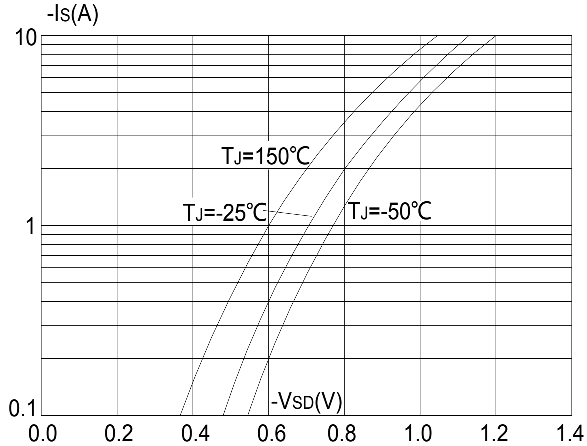


Figure 5: Gate Charge Characteristics

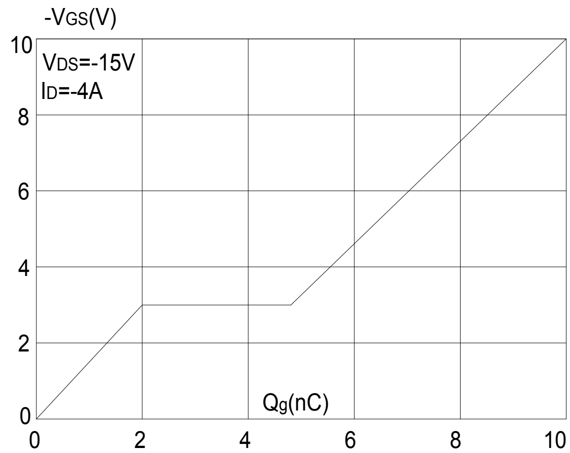


Figure 6: Capacitance Characteristics

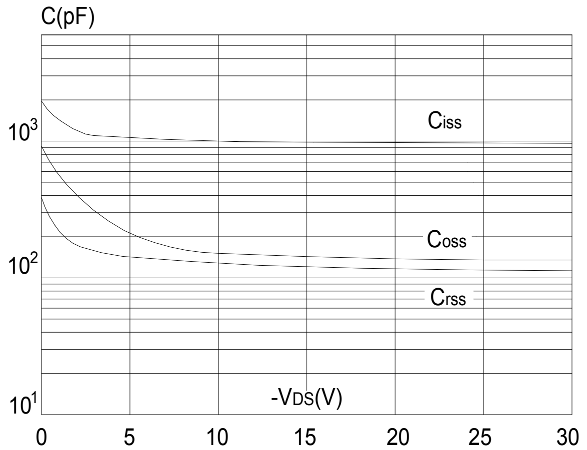


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

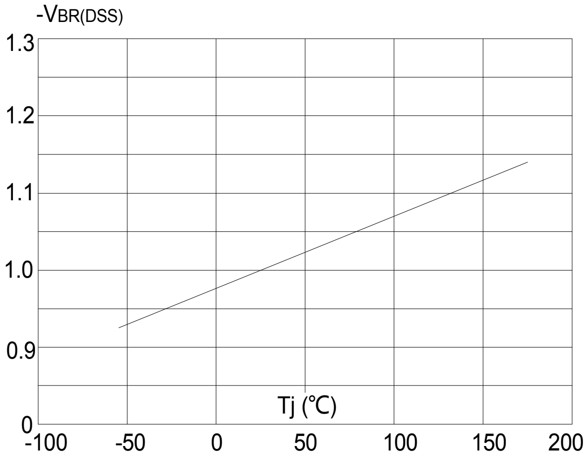


Figure 8: Normalized on Resistance vs. Junction Temperature

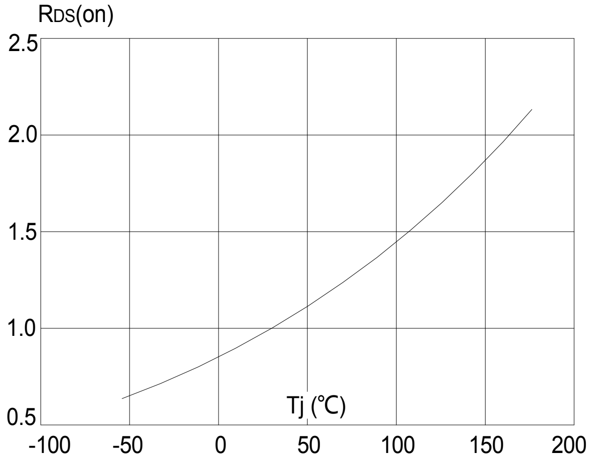


Figure 9: Maximum Safe Operating Area

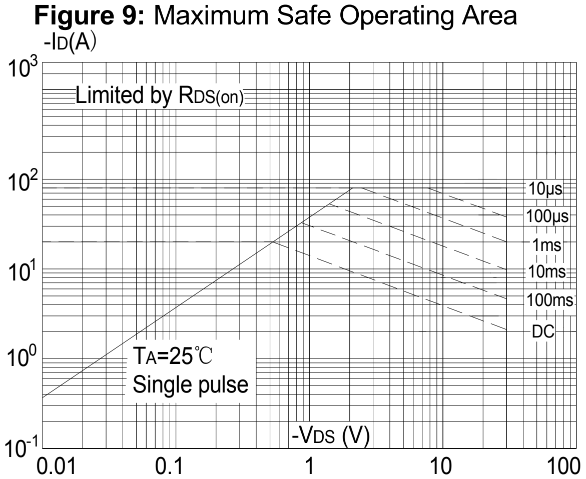


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

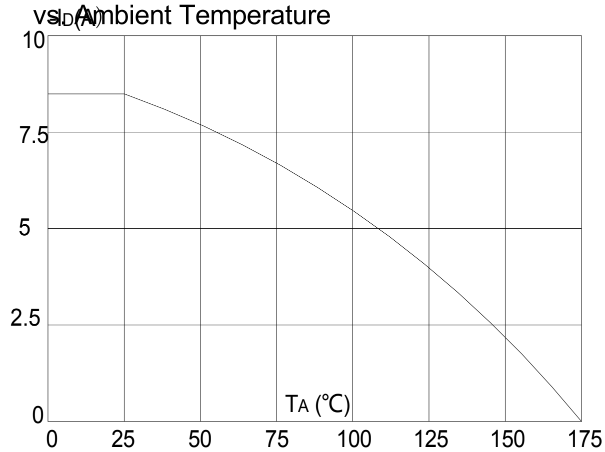
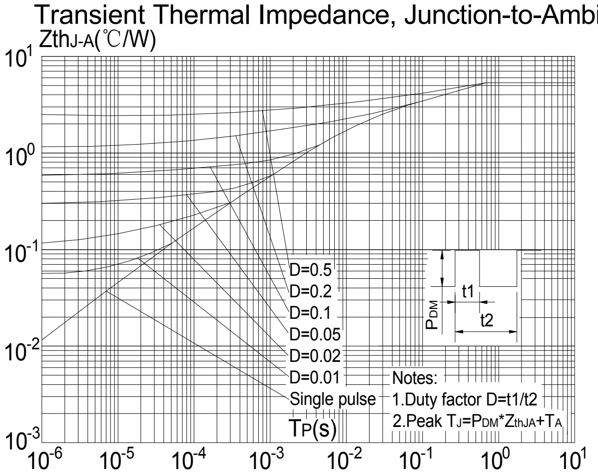
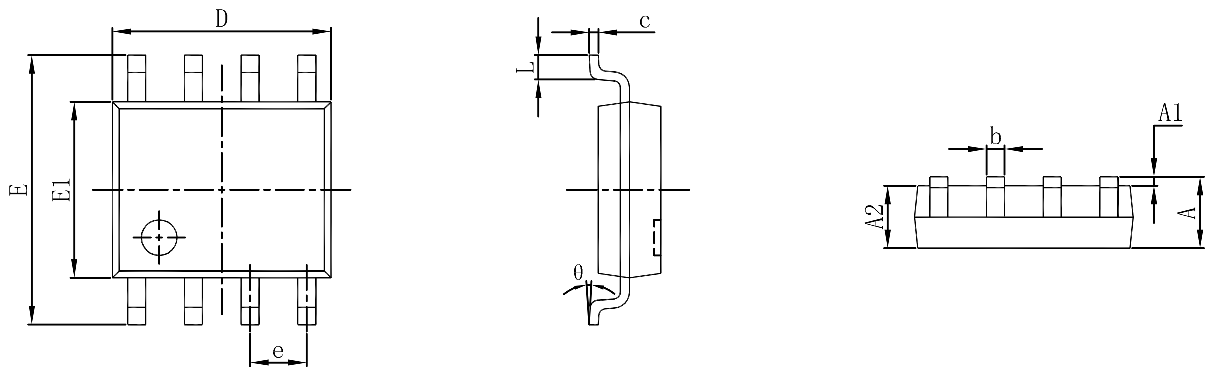


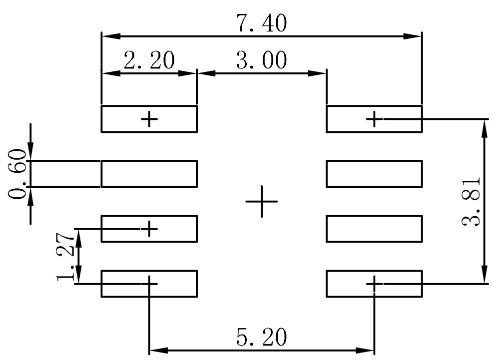
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270（BSC）		0.050（BSC）	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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